



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

OHTAKE, Fumio et al.

Serial No.: 09/749,590

Filed: December 28, 2000

For: SEMICONDUCTOR DEVICE HAVING GATE ELECTRODES WITH POLYMETAL STRUCTURE OF POLYCRYSTALLINE SILICON FILMS AND METAL FILMS (as amended)

Corres. and Mail

BOX AF

Group Art Unit: 2814

Examiner: MAI, Anh D.

P.T.O. Confirmation No.: 4831

3-18-03

J. A. [Signature]
4/16/03
C. P. [Signature]

RESPONSE UNDER 37 CFR §1.116

- EXPEDITED RESPONSE -
GROUP ART UNIT 2814

BOX AF

Commissioner for Patents
Washington D.C. 20231

Sir:

In response to the Office Action dated December 16, 2002, please amend the above-identified application as follows:

March 11, 2003

TECHNOLOGY CENTER 2800

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MAR 14 2003

IN THE CLAIMS:

Please CANCEL claims 18 and 19 without prejudice or disclaimer.

Please AMEND claims as follows:

1. (Twice Amended) A semiconductor device comprising:

a pair of impurity diffused regions formed in a silicon substrate, spaced from each other; and